

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

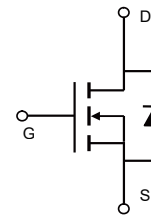
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- $V_{DS} = 120V, I_D = 60A$
 $R_{DS(ON)} = 11m\Omega$, typical @ $V_{GS} = 10V$
 $R_{DS(ON)} = 14m\Omega$, typical @ $V_{GS} = 4.5V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating



TO-252



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VST12N110	VST12N110-T2	TO-252	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	120	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	60	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	42	A
Pulsed Drain Current	I_{DM}	240	A
Maximum Power Dissipation	P_D	90	W
Derating factor		0.6	W/ $^\circ C$
Single pulse avalanche energy (Note 4)	E_{AS}	231	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.67	$^\circ C/W$
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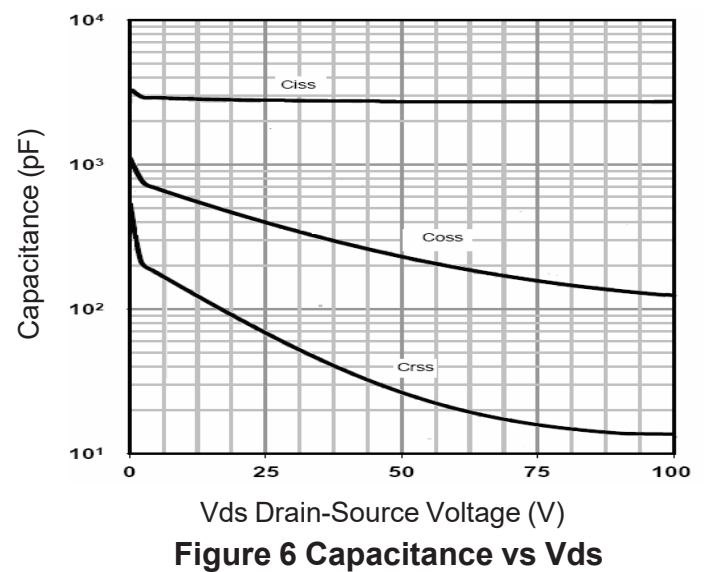
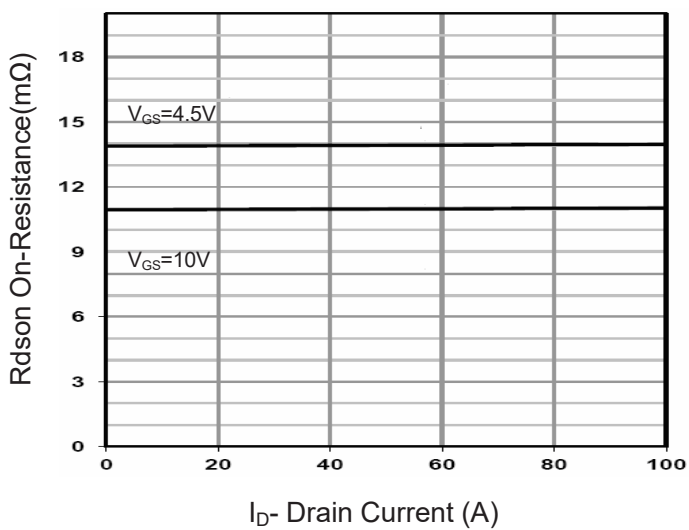
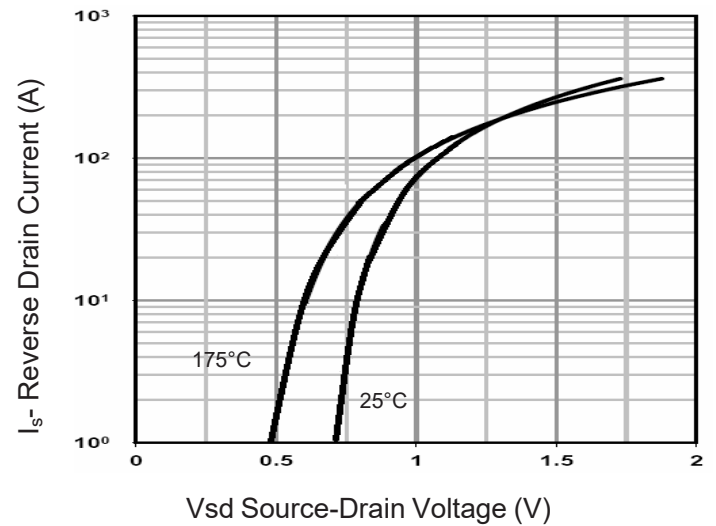
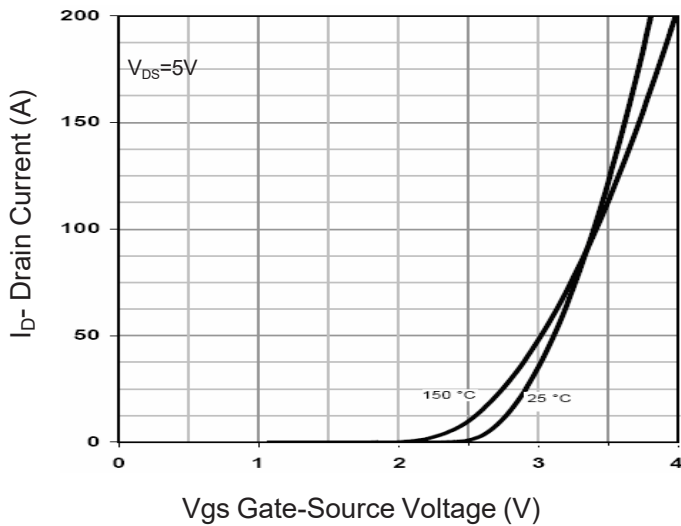
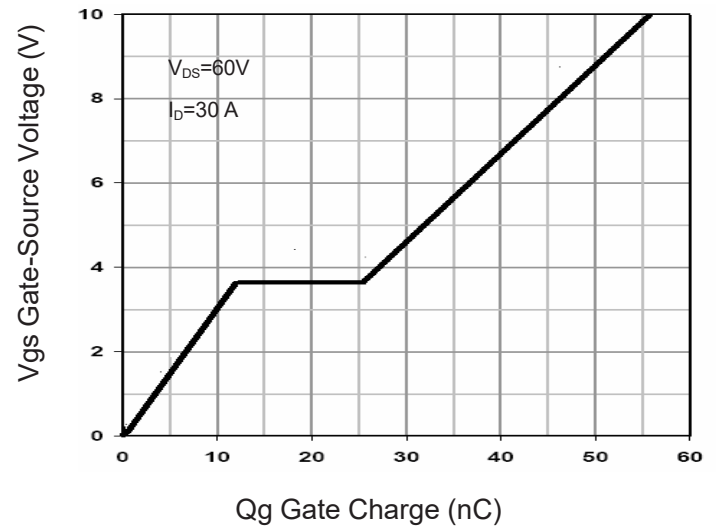
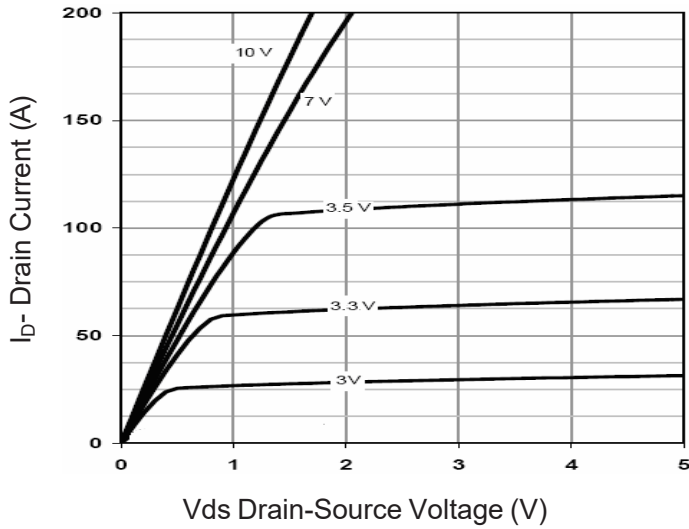
Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	120		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=120V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.1	1.7	2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=30A$	-	11	12	m Ω
		$V_{GS}=4.5V, I_D=30A$	-	14	15.5	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=30A$		60	-	S
Dynamic Characteristics (Note3)						
Input Capacitance	C_{iss}	$V_{DS}=60V, V_{GS}=0V,$ $F=1.0MHz$	-	2800	-	pF
Output Capacitance	C_{oss}		-	180	-	pF
Reverse Transfer Capacitance	C_{rss}		-	20	-	pF
Switching Characteristics (Note 3)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=60V, I_D=30A$ $V_{GS}=10V, R_G=1.6\Omega$	-	13	-	nS
Turn-on Rise Time	t_r		-	10	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	30	-	nS
Turn-Off Fall Time	t_f		-	8	-	nS
Total Gate Charge	Q_g	$V_{DS}=60V, I_D=30A,$ $V_{GS}=10V$	-	56	-	nC
Gate-Source Charge	Q_{gs}		-	12.5	-	nC
Gate-Drain Charge	Q_{gd}		-	14	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 2)	V_{SD}	$V_{GS}=0V, I_S=30A$	-	-	1.2	V
Diode Forward Current	I_S		-	-	60	A
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}C, I_F = 30A$ $di/dt = 100A/\mu s^{(Note3)}$	-	60	-	nS
Reverse Recovery Charge	Q_{rr}		-	106	-	nC

Notes:

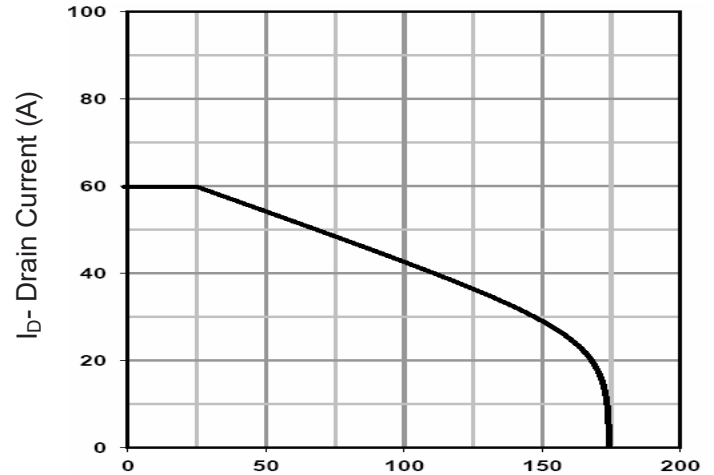
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
3. Guaranteed by design, not subject to production
4. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_{GS}=10V, L=0.25mH, R_G=25\Omega$

Typical Electrical and Thermal Characteristics

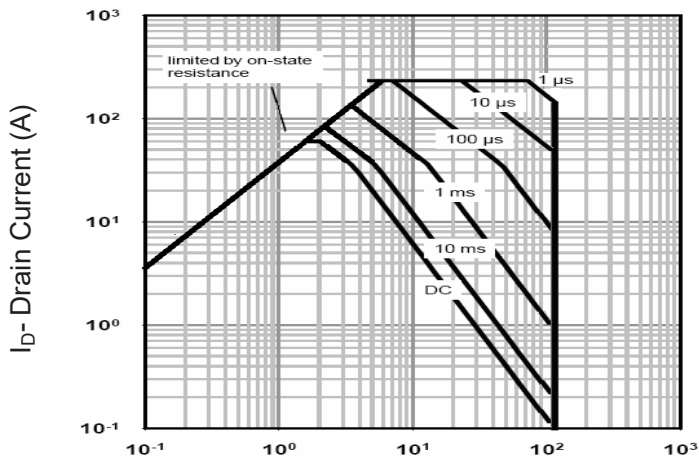




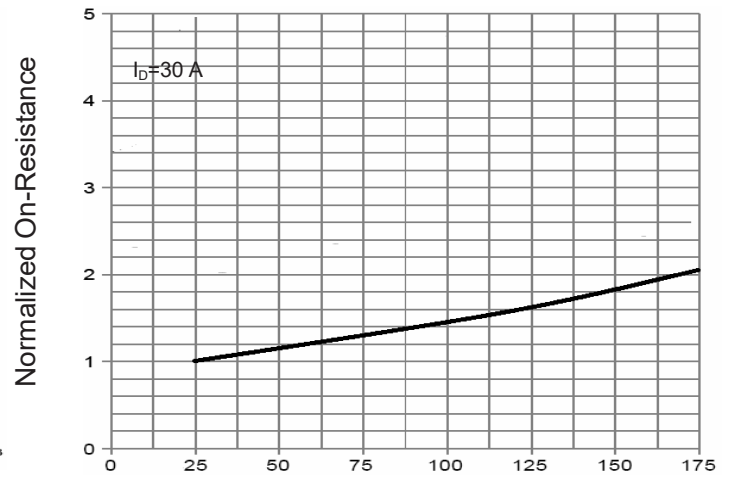
T_J -Junction Temperature(°C)
Figure 7 Power De-rating



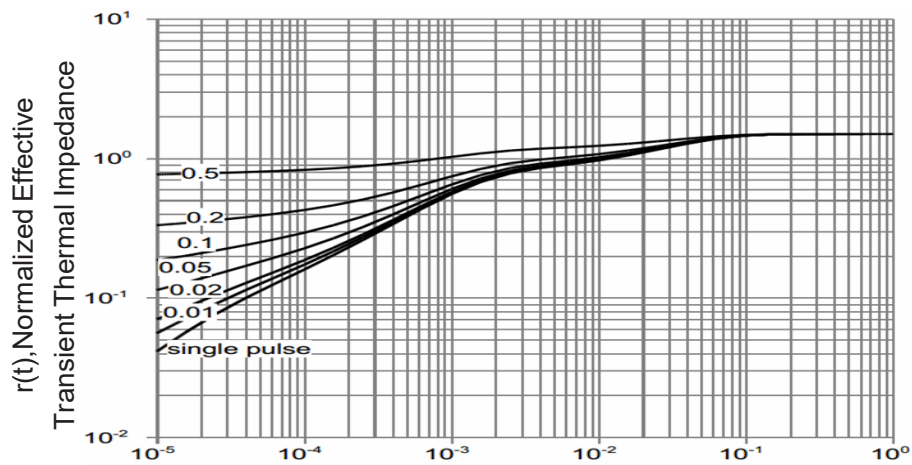
T_J -Junction Temperature (°C)
Figure 9 Current De-rating



V_{ds} Drain-Source Voltage (V)
Figure 8 Safe Operation Area



T_J -Junction Temperature(°C)
Figure 10 Rdson-Junction Temperature



Square Wave Pluse Duration(sec)
Figure 11 Normalized Maximum Transient Thermal Impedance